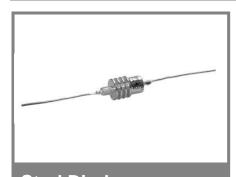
SKN 2,5



Stud Diode

Rectifier Diode

SKN 2,5

Features

- Reverse voltages up to 1600 V
- Hermetic metal case with glass insulator
- Anode side threaded stud ISO M4 (with lead wire in addition)
- SKN: anode to stud

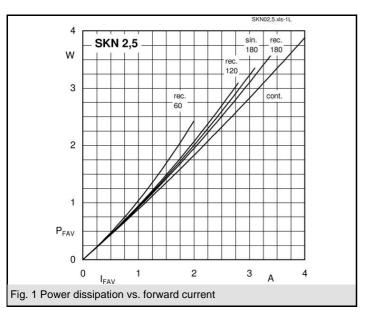
Typical Applications

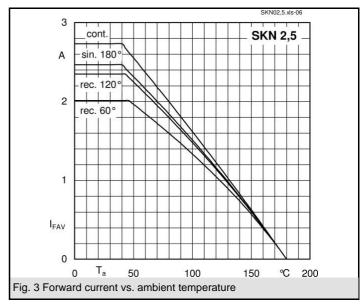
- All-purpose rectifier diodes
- For severe ambient conditions
- Recommended snubber network: RC: 0,02 μ F, 500 Ω (P $_{R}$ = 1 W) R $_{P}$ = 270 k Ω (P $_{R}$ = 2 W)

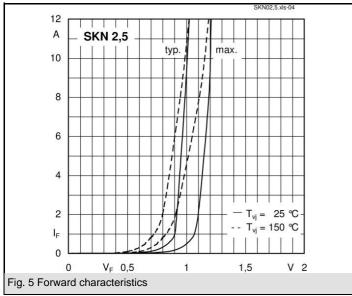
V _{RSM}	V _{RRM}	I _{FRMS} = 5 A (maximum value for continuous operation)	
V	V	$I_{FAV} = 2.5 \text{ A (sin. 180; T}_a = 45 \text{ °C)}$	
400	400	SKN 2,5/04	
800	800	SKN 2,5/08	
1200	1200	SKN 2,5/12	
1600	1600	SKN 2,5/16	

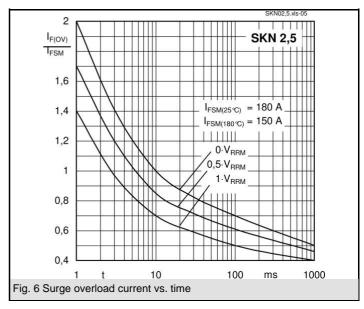
Symbol	Conditions	Values	Units
I _{FAV}	sin. 180; T _a = 45 (85) °C	2,5 (1,8)	А
I _{FSM}	T _{vi} = 25 °C; 10 ms	180	Α
	T _{vi} = 180 °C; 10 ms	150	Α
i²t	T _{vj} = 25 °C; 8,3 10 ms	160	A²s
	T _{vj} = 180 °C; 8,3 10 ms	110	A²s
V _F	T _{vi} = 25 °C; I _F = 10 A	max. 1,2	V
$V_{(TO)}$	T _{vi} = 180 °C	max. 0,85	V
r _T	T _{vi} = 180 °C	max. 30	mΩ
I_{RD}	$T_{vj} = 180 ^{\circ}\text{C}; V_{RD} = V_{RRM}$	max. 1,5	mA
Q_{rr}	$T_{vj} = 160 ^{\circ}\text{C}; - di_{F}/dt = 10 \text{A/}\mu\text{s}$	15	μC
R _{th(j-c)}		2,5	K/W
R _{th(j-a)}		55	K/W
T _{vj}		- 40 + 180	°C
T _{stg}		- 55 + 180	°C
V _{isol}		-	V~
M _s	to heatsink	0,8	Nm
а		5 * 9,81	m/s²
m	approx.	6	g
Case		E 5	

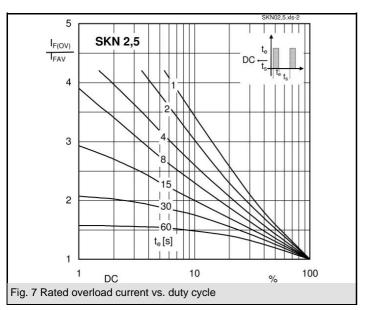


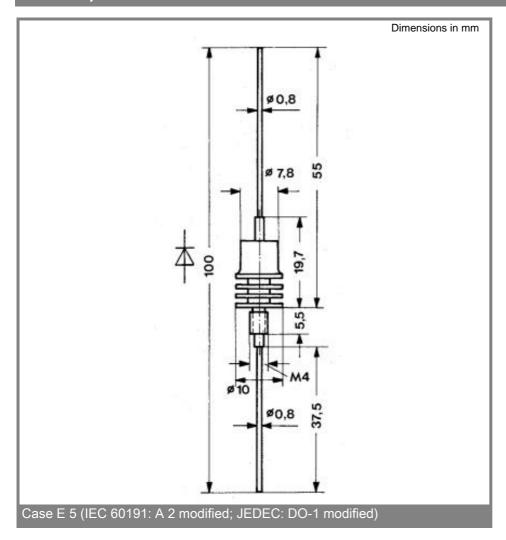












This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.